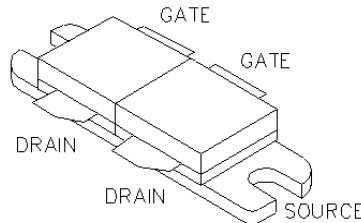




**General Description**

Silicon VDMOS and LDMOS transistors designed specifically for broadband RF applications. Suitable for Military Radios, Cellular and Paging Amplifier Base Stations, Broadcast FM/AM, MRI, Laser Driver and others.

"Polyfet"<sup>TM</sup> process features gold metal for greatly extended lifetime. Low output capacitance and high  $F_t$  enhance broadband performance



**PATENTED GOLD METALIZED SILICON GATE ENHANCEMENT MODE RF POWER VDMOS TRANSISTOR**

**100 Watts Gemini**

**Package Style AH**

**HIGH EFFICIENCY, LINEAR, HIGH GAIN, LOW NOISE**

**ABSOLUTE MAXIMUM RATINGS (TC = 25 °C)**

Total Device Dissipation	Junction to Case Thermal Resistance	Maximum Junction Temperature	Storage Temperature	DC Drain Current	Drain to Gate Voltage	Drain to Source Voltage	Gate to Source Voltage
350 Watts	0.5 °C/W	200 °C	-65 °C to 150 °C	16 A	70 V	70V	30V

**RF CHARACTERISTICS ( 100WATTS OUTPUT )**

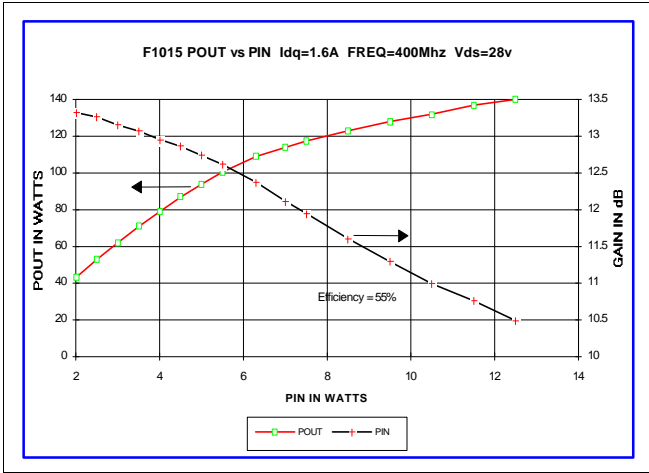
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Gps	Common Source Power Gain	12			dB	$I_{dq} = 1.6 A, V_{ds} = 28.0V, F = 400 MHz$
$\eta$	Drain Efficiency		60		%	$I_{dq} = 1.6 A, V_{ds} = 28.0V, F = 400 MHz$
VSWR	Load Mismatch Tolerance			20:1	Relative	$I_{dq} = 1.6 A, V_{ds} = 28.0V, F = 400 MHz$

**ELECTRICAL CHARACTERISTICS (EACH SIDE)**

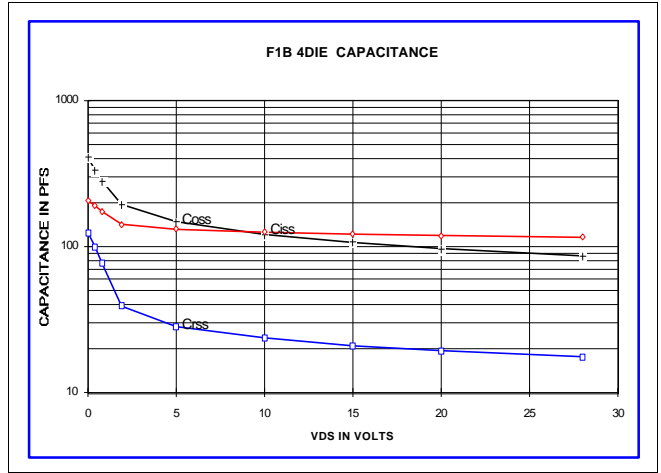
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Bvdss	Drain Breakdown Voltage	65			V	$I_{ds} = 0.2 A, V_{gs} = 0V$
Idss	Zero Bias Drain Current			4	mA	$V_{ds} = 28.0 V, V_{gs} = 0V$
Igss	Gate Leakage Current			1	uA	$V_{ds} = 0 V, V_{gs} = 30V$
Vgs	Gate Bias for Drain Current	1		7	V	$I_{ds} = 0.4 A, V_{gs} = V_{ds}$
gM	Forward Transconductance		3.2		Mho	$V_{ds} = 10V, V_{gs} = 5V$
Rdson	Saturation Resistance		0.35		Ohm	$V_{gs} = 20V, I_{ds} = 16A$
Idsat	Saturation Current		22		Amp	$V_{gs} = 20V, V_{ds} = 10V$
Ciss	Common Source Input Capacitance		132		pF	$V_{ds} = 28.0 V, V_{gs} = 0V, F = 1 MHz$
Crss	Common Source Feedback Capacitance		16		pF	$V_{ds} = 28.0 V, V_{gs} = 0V, F = 1 MHz$
Coss	Common Source Output Capacitance		80		pF	$V_{ds} = 28.0 V, V_{gs} = 0V, F = 1 MHz$

# F1015

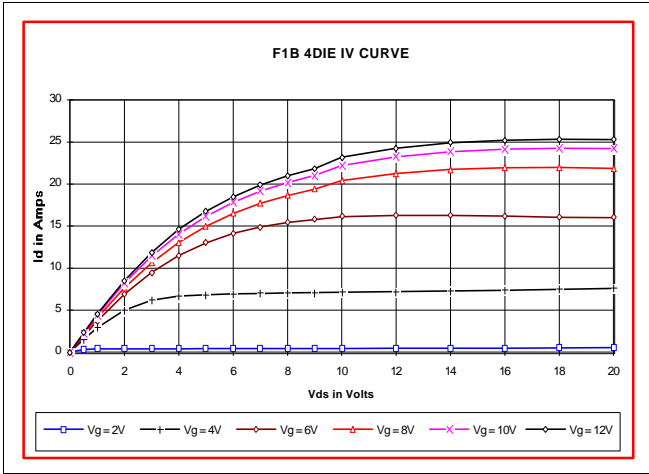
POUT VS PIN GRAPH



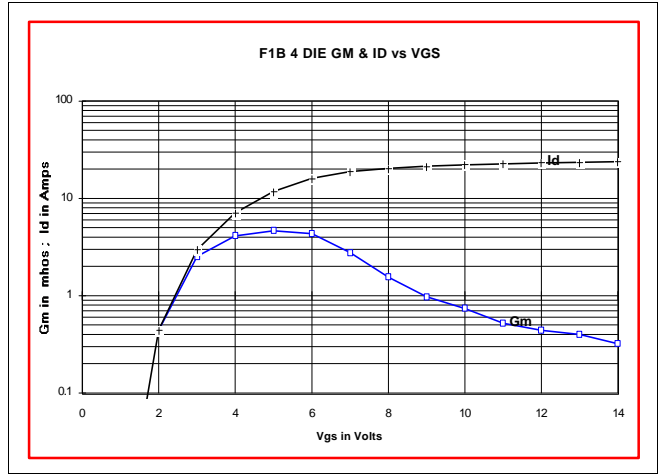
CAPACITANCE VS VOLTAGE



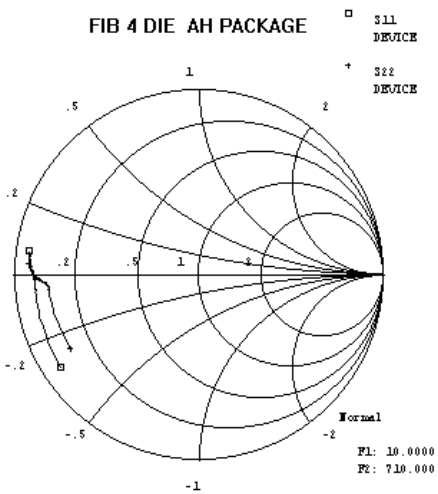
IV CURVE



ID AND GM VS VGS



S11 AND S22 SMITH CHART



PACKAGE DIMENSIONS IN INCHES

